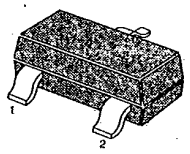
BCW32 NPN EPITAXIAL SILICON TRANSISTOR

T-29-19

GENERAL PURPOSE TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

• Refer to MMBT5088 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=10μA, I_E=0	30		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=2mA, I_B=0	20		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=10μA, I_C=0	5		V
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=2.0mA	200	450	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=10mA, I_B=0.5mA		0.25	V
Base-Emitter On Voltage	V_{BE} (on)	I_C=2mA, V_{CE}=5V	0.55	0.7	V
Output Capacitance	Cob	V_{CB}=10V, I_E=0 f=1.0MHz		4	pF
Noise Figure	NF	I_C=0.2mA, V_{CE}=5V R_S=2KΩ, f=1KHz		10	dB

Marking